



GP/1762  
PATENT

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8-2-02

Case Docket No. SEPP17.001AUS  
Date: July 26, 2002

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

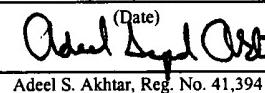
Applicant(s) : Ninisto et al.

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Appl. No. : 10/067,634

July 26, 2002

Filed : February 4, 2002

  
Adeel S. Akhtar, Reg. No. 41,394

For : METHOD OF DEPOSITING  
RARE EARTH OXIDE THIN  
FILMS

Examiner : Unknown

Group Art Unit : 1762

TRANSMITTAL LETTER

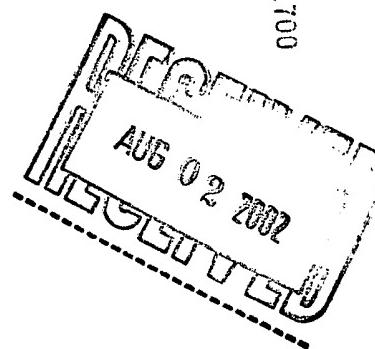
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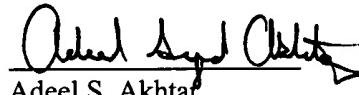
ATTENTION: APPLICATION BRANCH

Dear Sir:

Enclosed for filing in the above-identified application are:

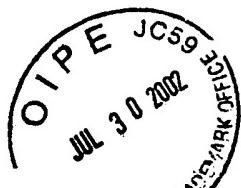
- (X) An Information Disclosure Statement.
- (X) A PTO Form 1449 with Thirteen (13) references.
- (X) The Commissioner is hereby authorized to charge any additional fees which may be required, or credit any overpayment, to Account No. 11-1410.
- (X) Return prepaid postcard.



  
Adeel S. Akhtar  
Registration No. 41,394  
Attorney of Record

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PATENT

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INFORMATION DISCLOSURE STATEMENT

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Dear Sir:

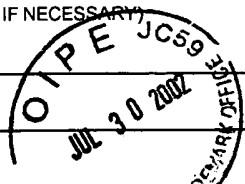
Enclosed is form PTO-1449 listing 13 references that are also enclosed. This Information Disclosure Statement is being filed before the receipt of a first Office Action on the merits, and presumably no fee is required in accordance with 37 C.F.R. § 1.97(b)(3). If a first Office Action on the merits was mailed before the mailing date of this Statement, the Commissioner is authorized to charge the fee set forth in 37 C.F.R. § 1.17(p) to Deposit Account No. 11-1410.

Respectfully submitted,  
KNOBBE, MARTENS, OLSON & BEAR, LLP

Dated: July 26, 2002

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FORM PTO-1449	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. SEPP17.001AUS	APPLICATION NO. 10/067,634
INFORMATION DISCLOSURE STATEMENT BY APPLICANT		APPLICANT Niinistö et al.	
(USE SEVERAL SHEETS IF NECESSARY)		FILING DATE February 4, 2002	GROUP 1762



U.S. PATENT DOCUMENTS						
EXAMINER INITIAL	DOCUMENT NUMBER	DATE RECEIVED	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
	4,058,430	11/15/77	Suntola et al.			
	5,711,811	01/27/98	Suntola et al.			

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)
	Mölsä, Heini, et al., "Growth of Yttrium Oxide Thin Films from $\beta$ -Diketonate Precursor," <i>Adv. Materials for Optics and Electronics</i> , 4: 389-400 (1994)
	Putkonen, Matti, et al., "Low-Temperature ALE Deposition of $Y_2O_3$ Thin Films from $\beta$ -Diketonate Precursors," <i>Chem. Vap. Deposition</i> , 7: 44-50 (2001)
	Hong, M., et al., "Epitaxial Cubic Gadolinium Oxide as a Dielectric for Gallium Arsenide Passivation," <i>Science</i> , 283:1897-1900 (1999)
	Seim, Helene, et al., "Growth of $LaCoO_3$ thin films from $\beta$ -Diketonate Precursors," <i>Appl. Surf. Science</i> , 112:243-250 (1997)
	Seim, Helene, et al., "Deposition of $LaNiO_3$ thin films in an atomic layer epitaxy reactor," <i>J. Mater. Chem.</i> , 7:449-454 (1997)
	Cho, M.-H, et al., "Growth stage of crystalline $Y_2O_3$ film on Si(100) grown by an ionized cluster beam deposition," <i>J. Appl. Phys.</i> , 85:2909-2914 (1999)
	Kingon, Angus I., et al., "Alternative dielectrics to silicon dioxide for memory and logic devices," <i>Nature</i> , 406:1032-1038 (2000)
	Nieminan, Minna et al., "Formation and stability of lanthanum oxide think films deposited from $\beta$ -diketonate precursor," <i>Appl. Surf. Science</i> , 174:155-165 (2001)
	Gaboriaud, R.J. et al., "Microstructural investigations of $Y_2O_3$ thin films deposited by laser ablation on $MgO$ ," <i>J. Appl. Phys. A</i> , 71:675-680 (2000)
	Ninistö, Laurie, "Advanced Thin Films For Electronics And Opto-Electronics By Atomic Layer Epitaxy," <i>Int'l Semiconductor Conf.</i> , 23rd Ed., Vol. 1, pp. 33-42 (2000)
	Suntola, Tuomo, "Atomic Layer Epitaxy," <i>Handbook of Crystal Growth</i> , Part B, Ch. 14, pp. 601-663

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EXAMINER	DATE CONSIDERED
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